
2SJ279(L), 2SJ279(S)

Silicon P-Channel MOS FET

HITACHI

November 1996

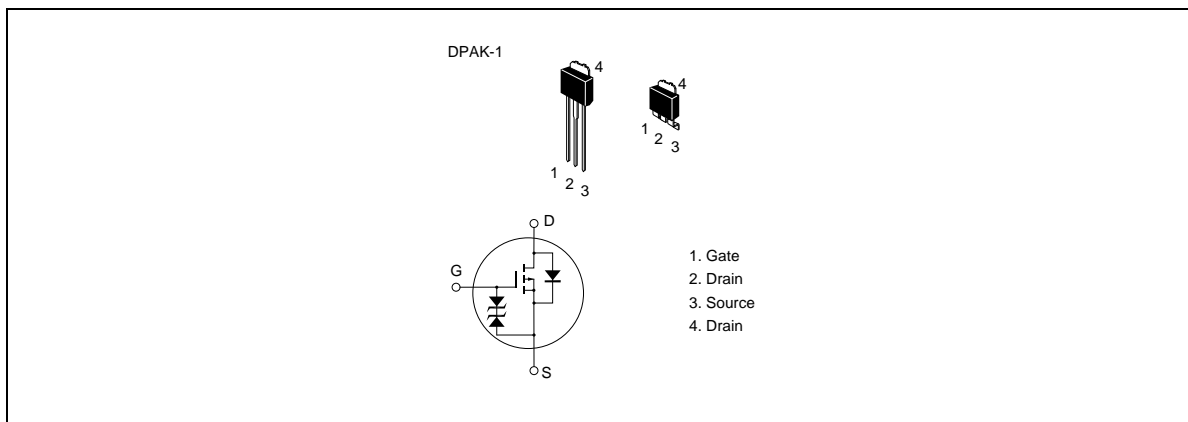
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device can be driven from 5 V source
- Suitable for switching regulator, DC-DC converter
- Avalanche ratings

Outline



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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	-60	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	-5	A
Drain peak current	$I_{D(pulse)}^{*1}$	-20	A
Body to drain diode reverse drain current	I_{DR}	-5	A
Avalanche current	I_{AP}^{*3}	-5	A
Avalanche energy	E_{AR}^{*3}	2.1	mJ
Channel dissipation	Pch^{*2}	20	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

- Notes
1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
 2. Value at $T_c = 25^\circ C$
 3. Value at $Tch = 25^\circ C$, $Rg \geq 50 \Omega$

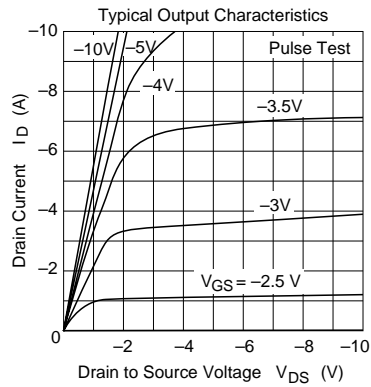
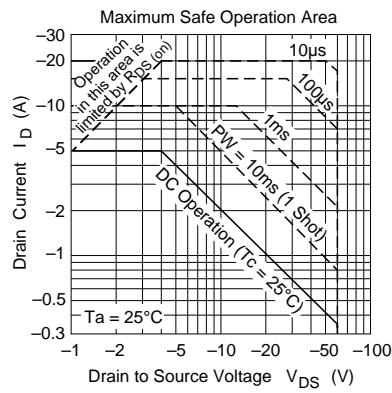
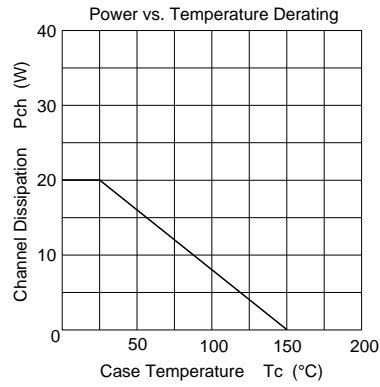
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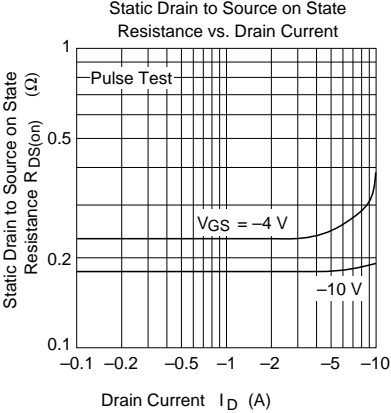
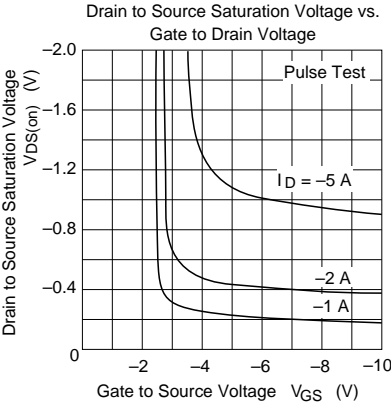
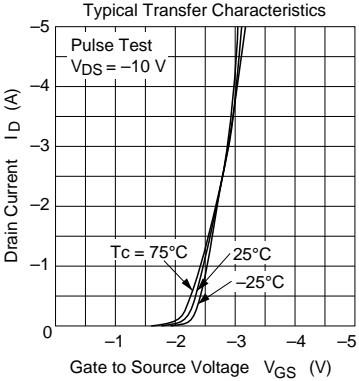
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-60	—	—	V	$I_D = -10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-100	μA	$V_{DS} = -50 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.25	V	$I_D = -1 \text{ mA}, V_{DS} = -10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.18	0.20	Ω	$I_D = -3 \text{ A}, V_{GS} = -10 \text{ V}^{*1}$
		—	0.23	0.27	Ω	$I_D = -3 \text{ A}, V_{GS} = -4 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	3.0	5	—	S	$I_D = -3 \text{ A}, V_{DS} = -10 \text{ V}^{*1}$
Input capacitance	C_{iss}	—	690	—	pF	$V_{DS} = -10 \text{ V}, V_{GS} = 0,$ $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	340	—	pF	
Reverse transfer capacitance	C_{rss}	—	110	—	pF	
Turn-on delay time	$t_{d(on)}$	—	15	—	ns	$I_D = -3 \text{ A}, V_{GS} = -10 \text{ V},$ $R_L = 10 \text{ }\Omega$
Rise time	t_r	—	35	—	ns	
Turn-off delay time	$t_{d(off)}$	—	125	—	ns	
Fall time	t_f	—	75	—	ns	
Body to drain diode forward voltage	V_{DF}	—	-1.2	—	V	$I_F = -5 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	140	—	μs	$I_F = -5 \text{ A}, V_{GS} = 0,$ $di_F/dt = 50 \text{ A}/\mu\text{s}$

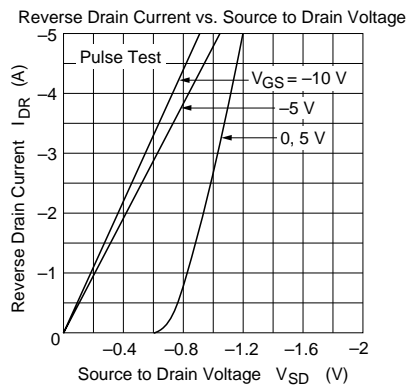
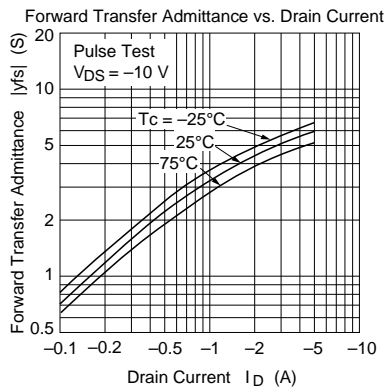
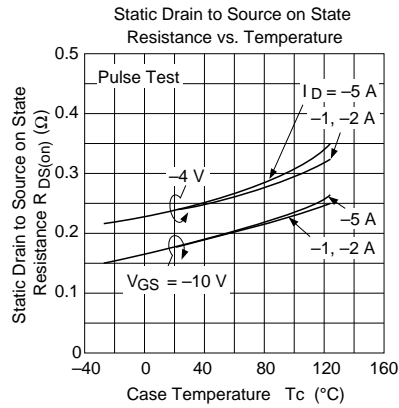
Note 1. Pulse test

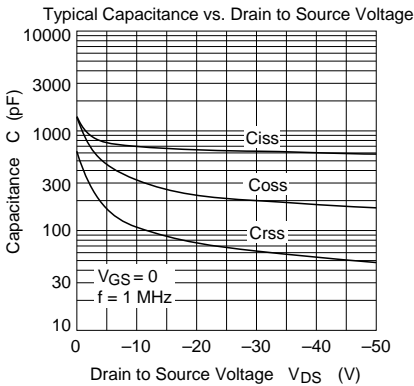
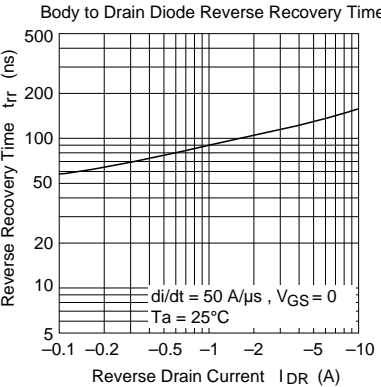
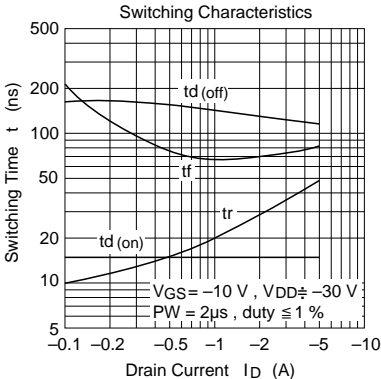
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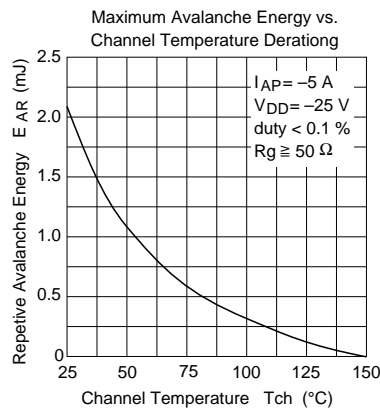
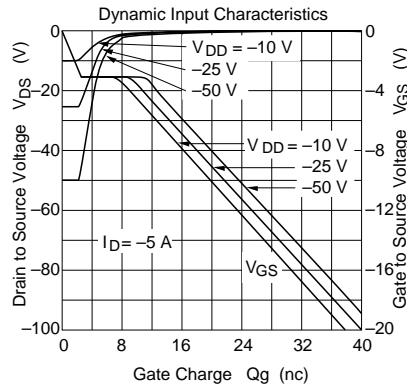


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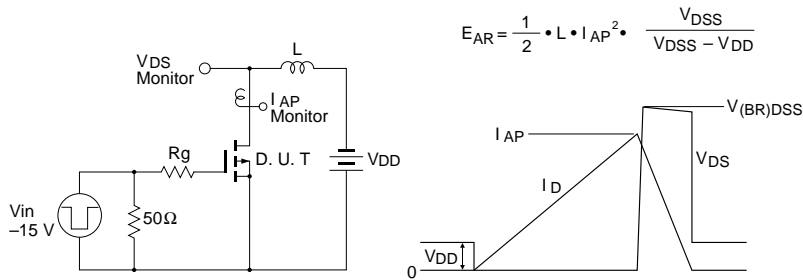


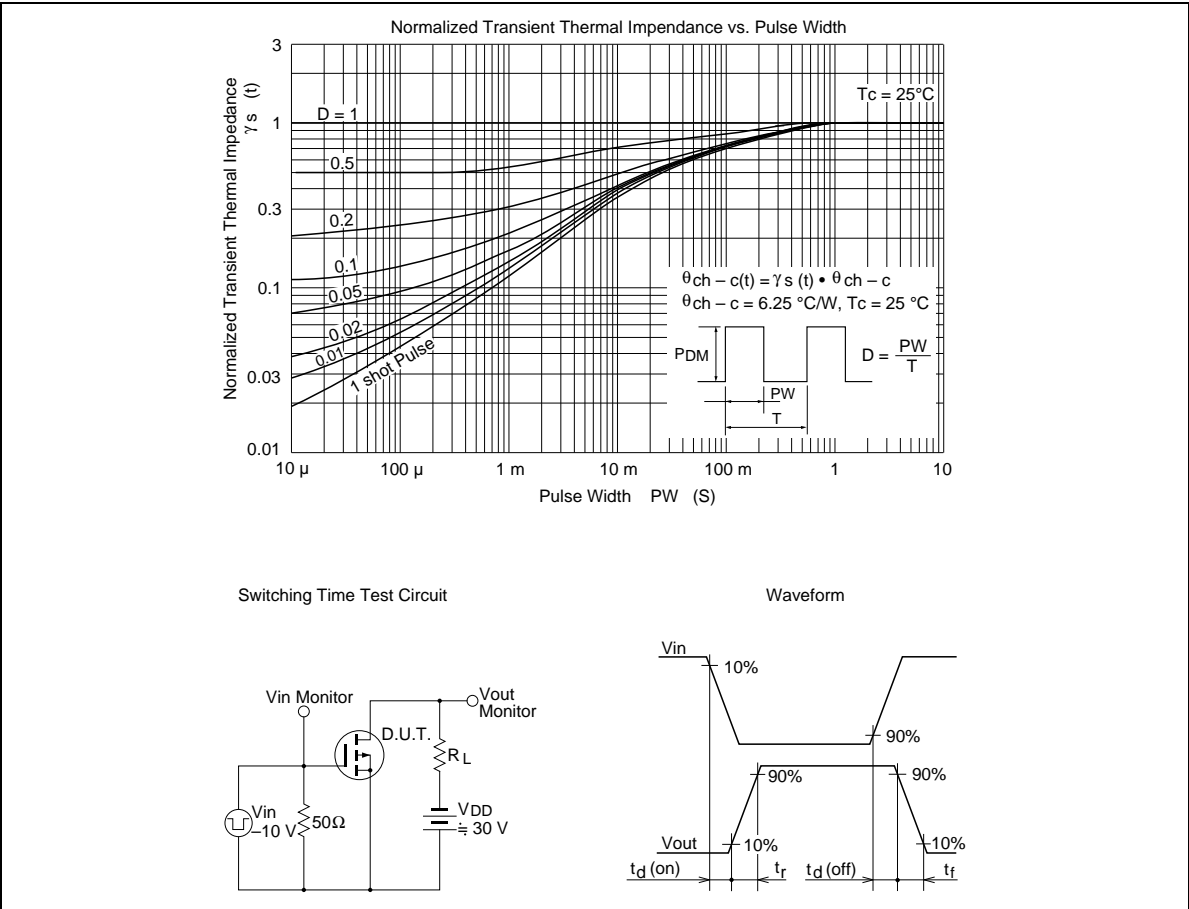


2SJ279(L), 2SJ279(S)



Avalanche Test Circuit and Waveform





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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohite-machi, Chiyoda-ku, Tokyo 100, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA. 94005-4935
U.S.A.
Tel: 415-589-8900
Fax: 415-589-4207

Hitachi Europe GmbH
Electronic Components Group
Continental Europe
Dannebergstrasse 3
D-85622 Feldkirchen
München
Tel: 089-9 94 80-0
Fax: 089-9 29 30 00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YU
United Kingdom
Tel: 0628-585000
Fax: 0628-778322

Hitachi Asia Pte. Ltd.
15 Collyer Quay #20-00
Hitachi Tower
Singapore 0404
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 706, North Tower,
World Finance Centre
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27308074